



# BTA202X-800D

3Q Hi-Com Triac

22 May 2014

Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT186A (TO-220F) "full pack" plastic package. The "series D" triac balances the requirements of commutation performance and gate sensitivity. This "very sensitive gate" "series D" is intended for interfacing with low power drivers including microcontrollers.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by  $dV/dt$
- High commutation capability with very sensitive gate
- High voltage capability
- Isolated mounting base package
- Planar technology for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very sensitive gate for easy logic level triggering

## 3. Applications

- General purpose motor controls
- Large and small appliances (White Goods)
- Loads such as contactors, circuit breakers, valves, dispensers and door locks
- Lower-power highly inductive, resistive and safety loads

## 4. Quick reference data

Table 1. Quick reference data

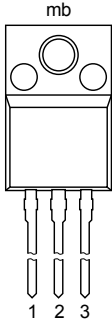
| Symbol                        | Parameter                            | Conditions                                                                                                                                 | Min  | Typ | Max | Unit |
|-------------------------------|--------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------|------|-----|-----|------|
| $V_{DRM}$                     | repetitive peak off-state voltage    |                                                                                                                                            | -    | -   | 800 | V    |
| $I_{TSM}$                     | non-repetitive peak on-state current | full sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -    | -   | 14  | A    |
| $I_{T(RMS)}$                  | RMS on-state current                 | full sine wave; $T_h \leq 110\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>          | -    | -   | 2   | A    |
| <b>Static characteristics</b> |                                      |                                                                                                                                            |      |     |     |      |
| $I_{GT}$                      | gate trigger current                 | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_2+$ G+; $T_j = 25\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 7</a>                        | 0.25 | -   | 5   | mA   |



| Symbol | Parameter | Conditions                                                                                                        | Min  | Typ | Max | Unit |
|--------|-----------|-------------------------------------------------------------------------------------------------------------------|------|-----|-----|------|
|        |           | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | 0.25 | -   | 5   | mA   |
|        |           | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> | 0.25 | -   | 5   | mA   |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description             | Simplified outline                                                                                          | Graphic symbol                                                                                    |
|-----|--------|-------------------------|-------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------|
| 1   | T1     | main terminal 1         |  <p>TO-220F (SOT186A)</p> |  <p>sym051</p> |
| 2   | T2     | main terminal 2         |                                                                                                             |                                                                                                   |
| 3   | G      | gate                    |                                                                                                             |                                                                                                   |
| mb  | n.c.   | mounting base; isolated |                                                                                                             |                                                                                                   |

## 6. Ordering information

Table 3. Ordering information

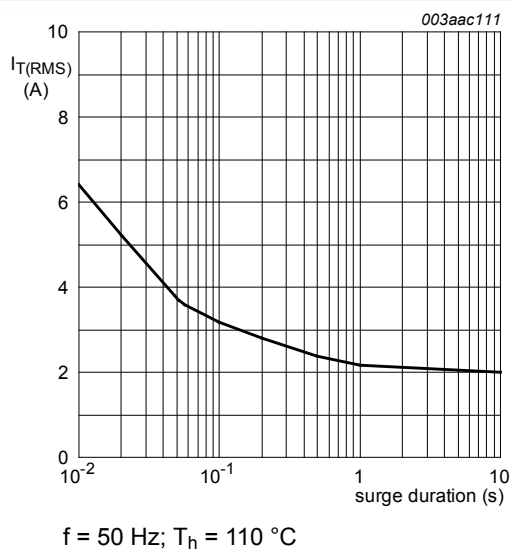
| Type number  | Package |                                                                                                     |         |
|--------------|---------|-----------------------------------------------------------------------------------------------------|---------|
|              | Name    | Description                                                                                         | Version |
| BTA202X-800D | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 "full pack" | SOT186A |

## 7. Limiting values

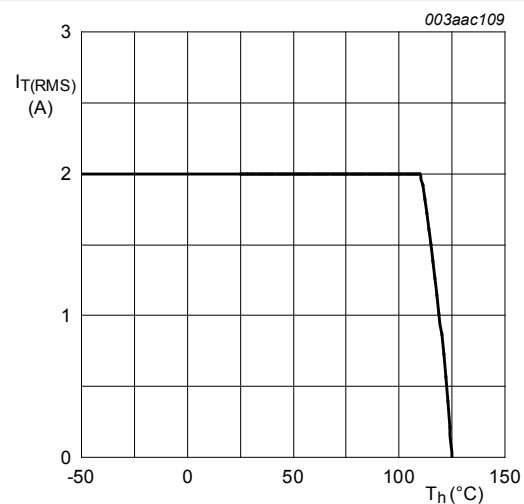
**Table 4. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

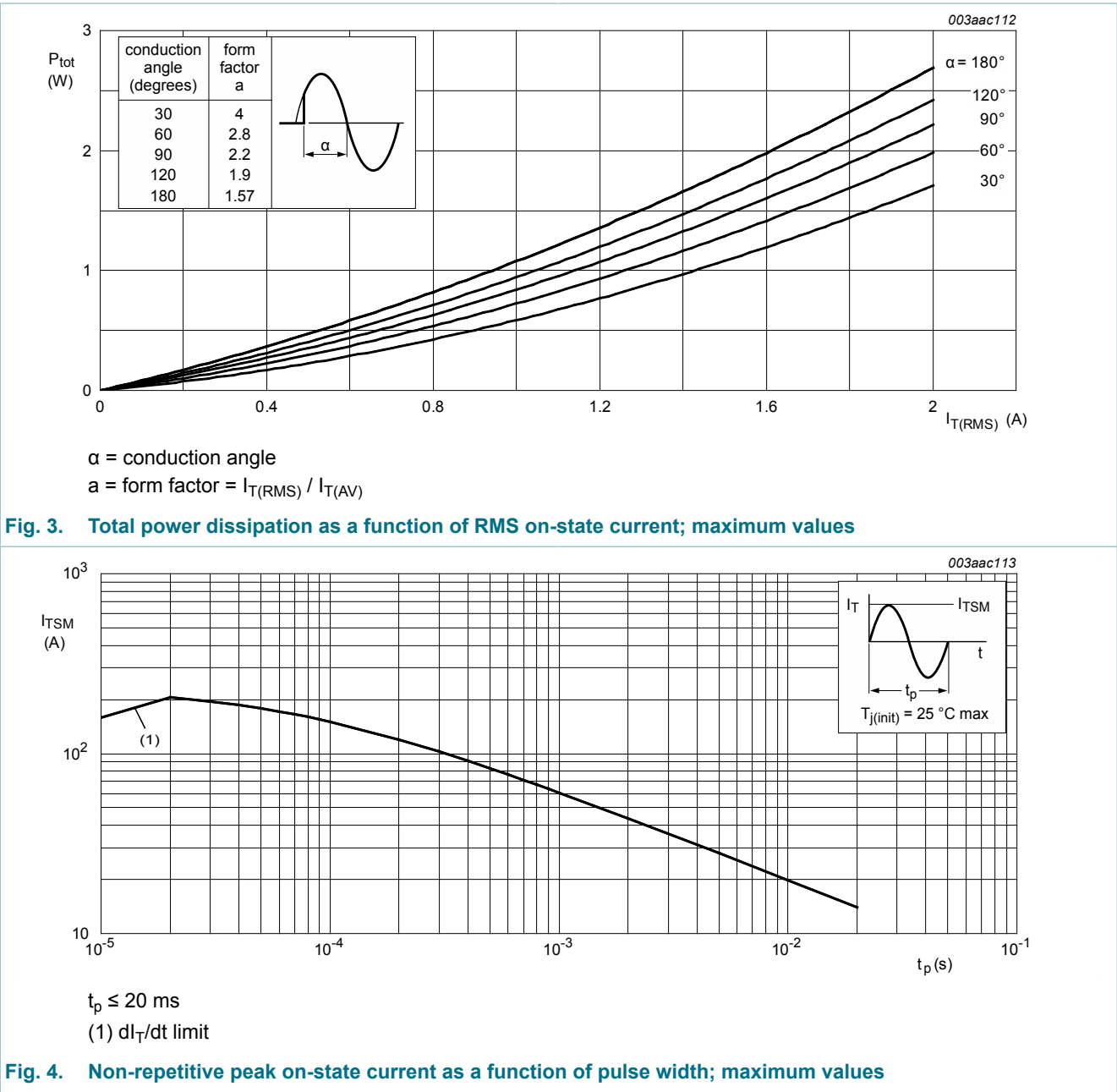
| Symbol              | Parameter                            | Conditions                                                                                                                                 | Min | Max  | Unit                   |
|---------------------|--------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------|-----|------|------------------------|
| $V_{\text{DRM}}$    | repetitive peak off-state voltage    |                                                                                                                                            | -   | 800  | V                      |
| $I_{\text{T(RMS)}}$ | RMS on-state current                 | full sine wave; $T_h \leq 110\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>          | -   | 2    | A                      |
| $I_{\text{TSM}}$    | non-repetitive peak on-state current | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | 14   | A                      |
|                     |                                      | full sine wave; $T_{\text{j(init)}} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 16.7\text{ ms}$                                                 | -   | 15.4 | A                      |
| $I^2t$              | $I^2t$ for fusing                    | $t_p = 10\text{ ms}$ ; SIN                                                                                                                 | -   | 0.98 | $\text{A}^2\text{s}$   |
| $dl_{\text{T}}/dt$  | rate of rise of on-state current     | $I_{\text{T}} = 1.5\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $dl_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$                              | -   | 100  | $\text{A}/\mu\text{s}$ |
| $I_{\text{GM}}$     | peak gate current                    |                                                                                                                                            | -   | 2    | A                      |
| $P_{\text{GM}}$     | peak gate power                      |                                                                                                                                            | -   | 5    | W                      |
| $P_{\text{G(AV)}}$  | average gate power                   | over any 20 ms period                                                                                                                      | -   | 0.5  | W                      |
| $T_{\text{stg}}$    | storage temperature                  |                                                                                                                                            | -40 | 150  | $^{\circ}\text{C}$     |
| $T_{\text{j}}$      | junction temperature                 |                                                                                                                                            | -   | 125  | $^{\circ}\text{C}$     |

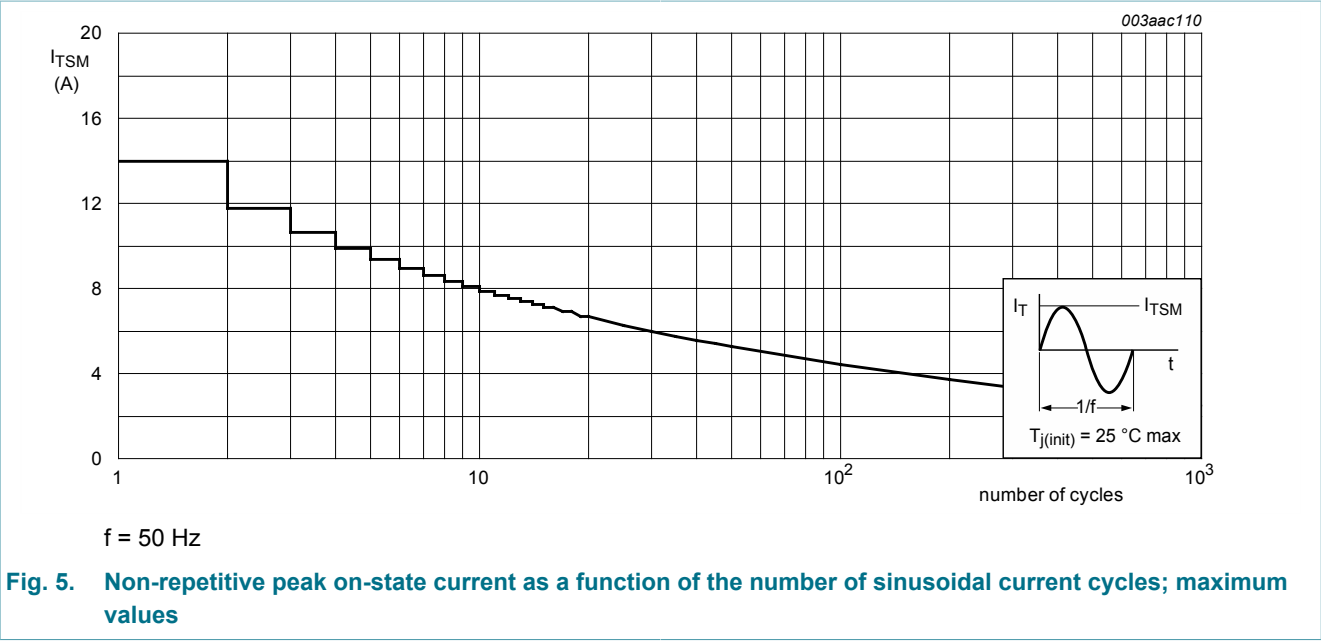


**Fig. 1. RMS on-state current as a function of surge duration; maximum values**



**Fig. 2. RMS on-state current as a function of heatsink temperature; maximum values**





## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol        | Parameter                                    | Conditions                                                 | Min | Typ | Max | Unit |
|---------------|----------------------------------------------|------------------------------------------------------------|-----|-----|-----|------|
| $R_{th(j-h)}$ | thermal resistance from junction to heatsink | full cycle; with heatsink compound; <a href="#">Fig. 6</a> | -   | -   | 5.5 | K/W  |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient  | in free air                                                | -   | 55  | -   | K/W  |

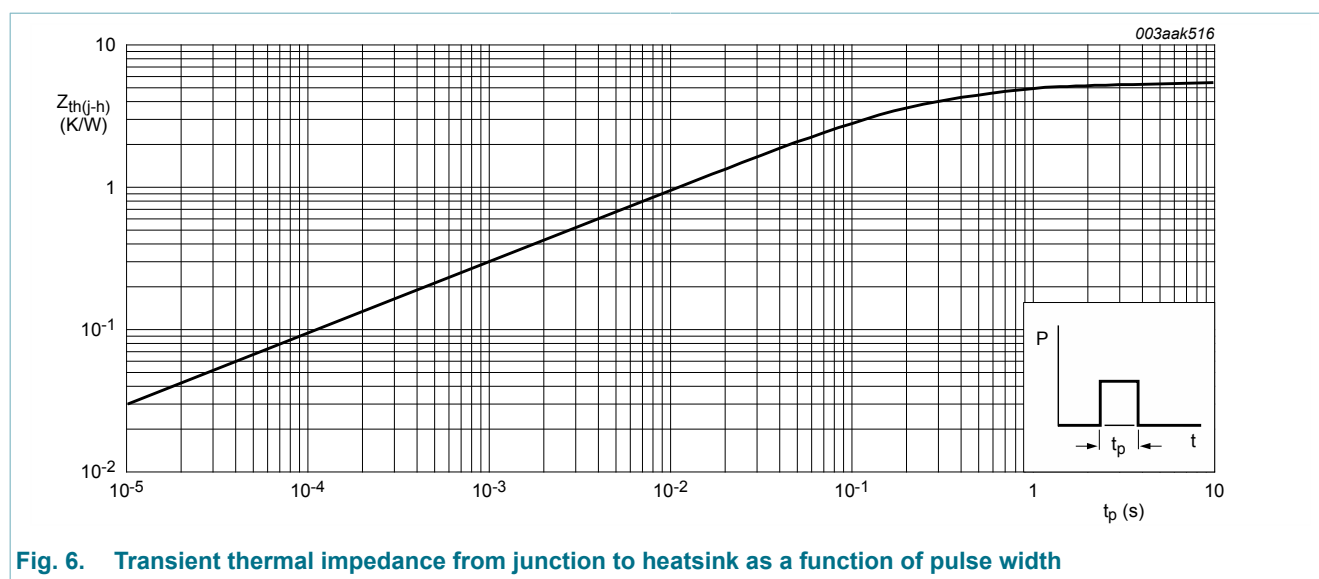


Fig. 6. Transient thermal impedance from junction to heatsink as a function of pulse width

## 9. Isolation characteristics

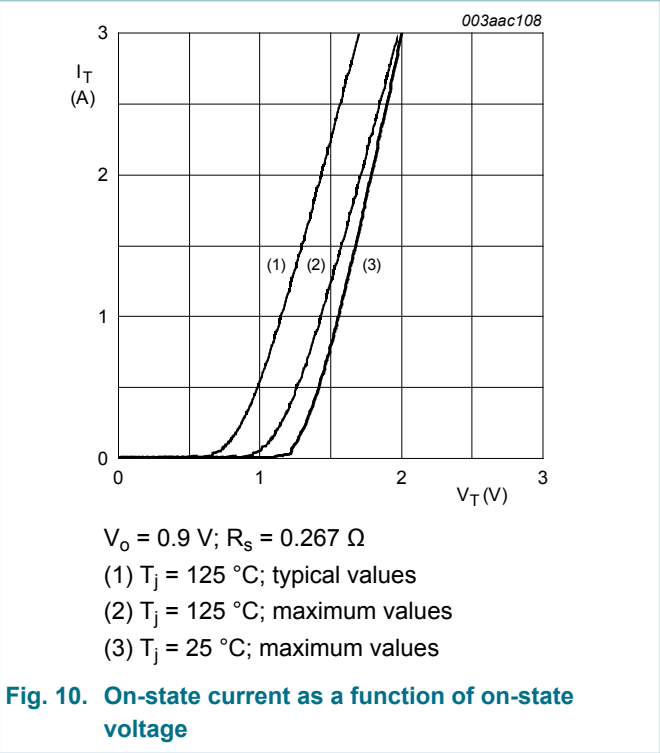
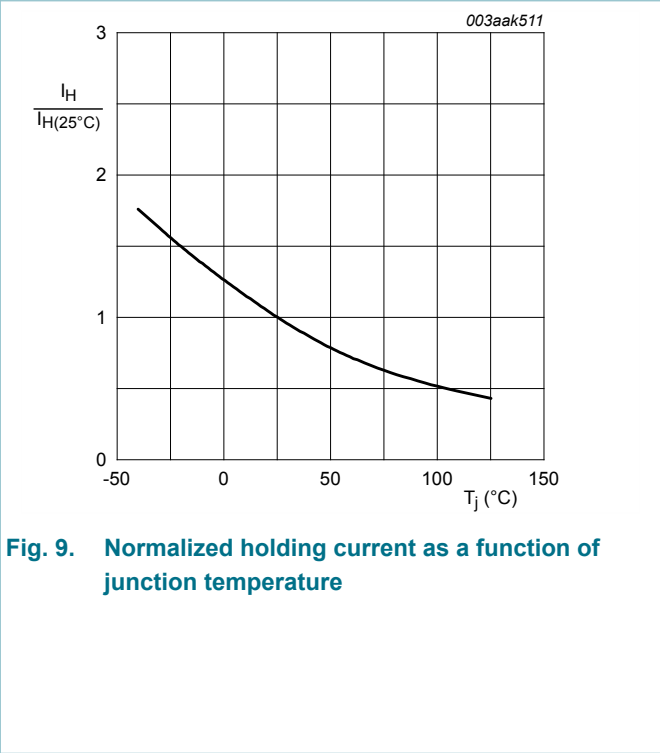
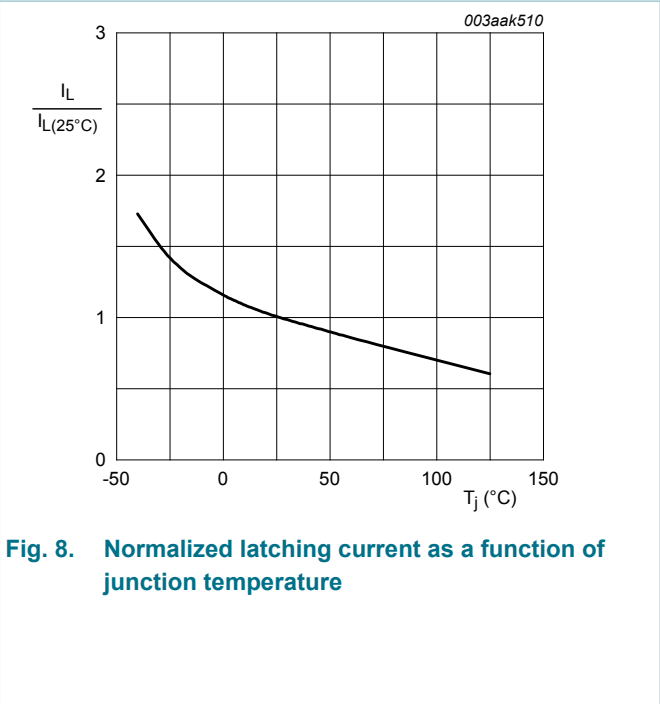
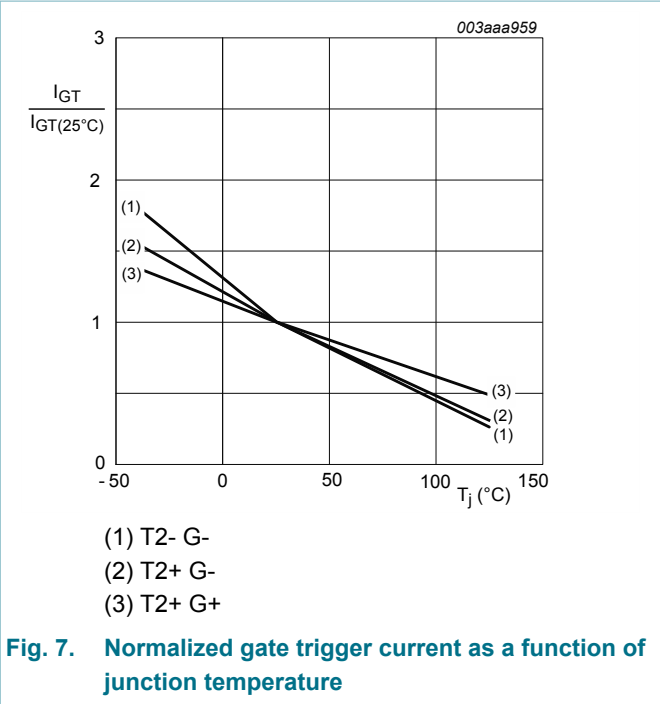
Table 6. Isolation characteristics

| Symbol          | Parameter             | Conditions                                                                                                                                                                     | Min | Typ | Max  | Unit |
|-----------------|-----------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|-----|------|------|
| $V_{isol(RMS)}$ | RMS isolation voltage | from all terminals to external heatsink; sinusoidal waveform; clean and dust free; $50\text{ Hz} \leq f \leq 60\text{ Hz}$ ; $RH \leq 65\%$ ; $T_h = 25\text{ }^\circ\text{C}$ | -   | -   | 2500 | V    |
| $C_{isol}$      | isolation capacitance | from main terminal 2 to external heatsink; $f = 1\text{ MHz}$                                                                                                                  | -   | 10  | -    | pF   |

## 10. Characteristics

Table 7. Characteristics

| Symbol                         | Parameter                             | Conditions                                                                                                                                                                     | Min  | Typ  | Max | Unit             |
|--------------------------------|---------------------------------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------|------|-----|------------------|
| <b>Static characteristics</b>  |                                       |                                                                                                                                                                                |      |      |     |                  |
| $I_{GT}$                       | gate trigger current                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                                                              | 0.25 | -    | 5   | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                                                              | 0.25 | -    | 5   | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>                                                              | 0.25 | -    | 5   | mA               |
| $I_L$                          | latching current                      | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                                                              | -    | -    | 5   | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                                                              | -    | -    | 10  | mA               |
|                                |                                       | $V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-;<br>$T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>                                                              | -    | -    | 5   | mA               |
| $I_H$                          | holding current                       | $V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>                                                                                                | -    | -    | 5   | mA               |
| $V_T$                          | on-state voltage                      | $I_T = 3\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>                                                                                                | -    | 1.63 | 2   | V                |
| $V_{GT}$                       | gate trigger voltage                  | $V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>                                                                     | -    | 0.7  | 1   | V                |
|                                |                                       | $V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ;<br><a href="#">Fig. 11</a>                                                                   | 0.2  | 0.3  | -   | V                |
| $I_D$                          | off-state current                     | $V_D = 800\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$                                                                                                                       | -    | 0.1  | 0.5 | mA               |
| <b>Dynamic characteristics</b> |                                       |                                                                                                                                                                                |      |      |     |                  |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ;<br>$R_{GT1} = 220\text{ }\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ );<br>exponential waveform                     | -    | 350  | -   | V/ $\mu\text{s}$ |
| $dI_{com}/dt$                  | rate of change of commutating current | $V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 2\text{ A}$ ;<br>$dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit | 1    | -    | -   | A/ms             |
|                                |                                       | $V_D = 400\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{T(RMS)} = 2\text{ A}$ ;<br>$dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit                          | 1.2  | -    | -   | A/ms             |





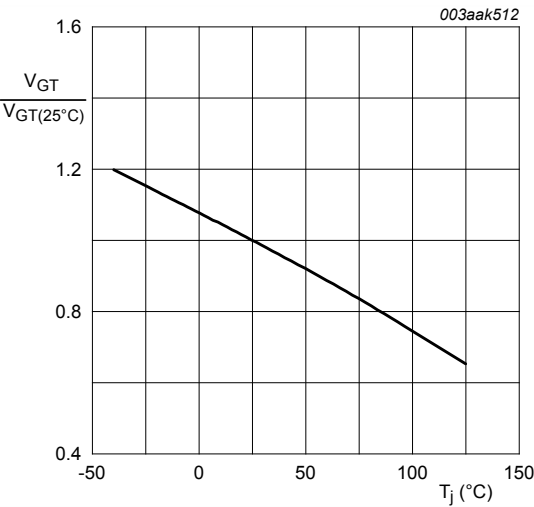


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

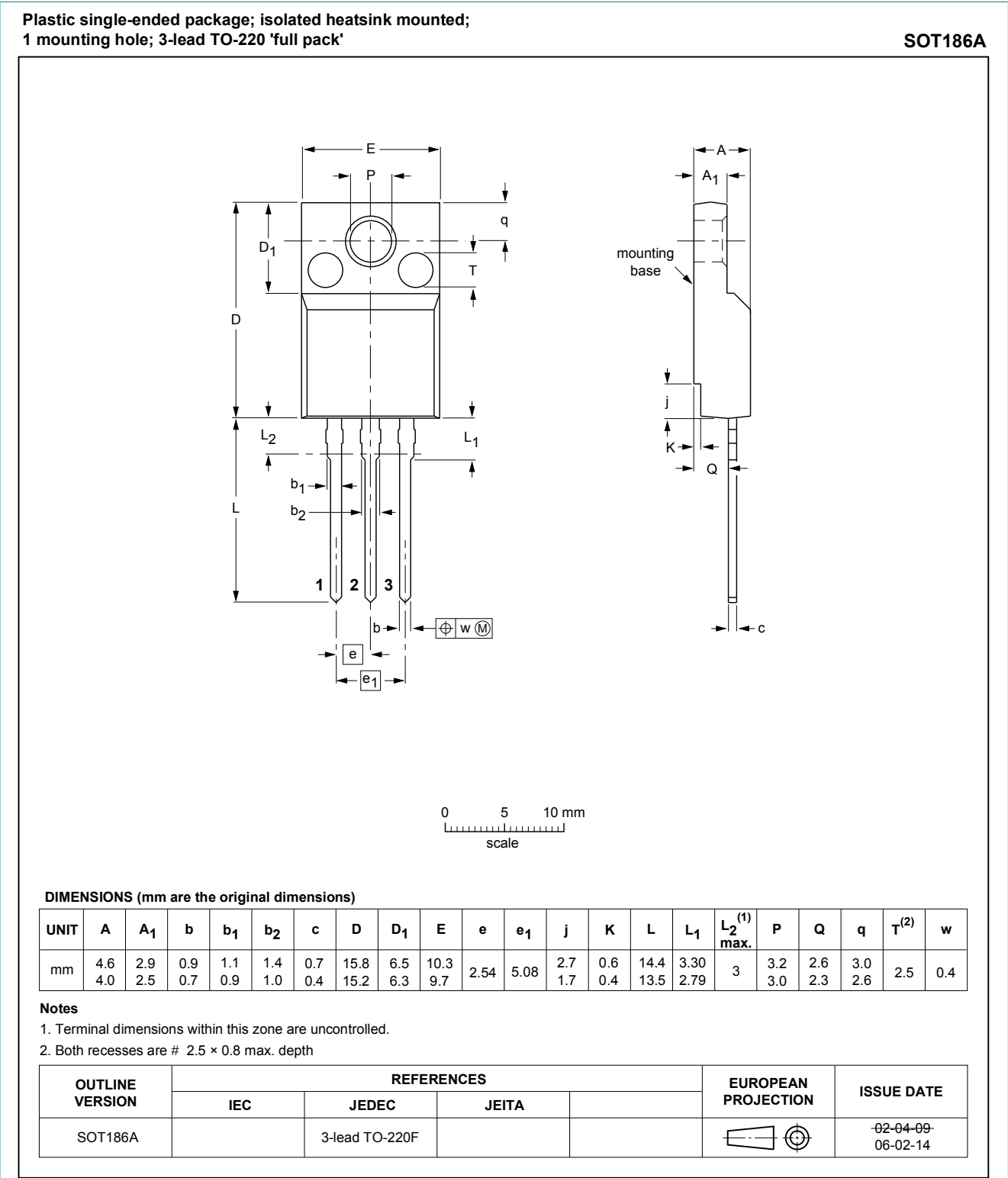


Fig. 12. Package outline TO-220F (SOT186A)

## 12. Legal information

### 12.1 Data sheet status

| Document status [1][2]         | Product status [3] | Definition                                                                            |
|--------------------------------|--------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
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